

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-20V	64mΩ@-4.5V	-4.0A
	80mΩ@-2.5V	
	110mΩ@-1.8V	

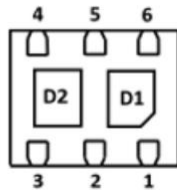
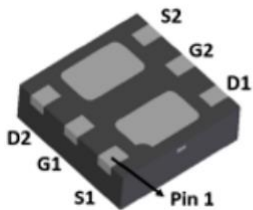
### Feature

- Advanced trench process technology
- High density cell design for ultra low on-resistance
- Suffix "-Q1" for AEC-Q101

### Application

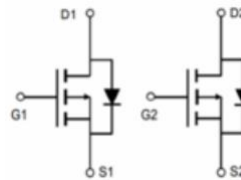
- Video monitor
- Power management

### Package

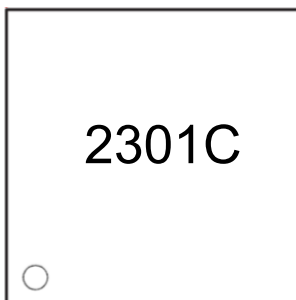


DFN2\*2-6L

### Circuit diagram



### Marking



### Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	±10	V
Continuous Drain Current	$I_D$	-4.0	A
Pulsed Drain Current	$I_{DM}$	-16	A
Power Dissipation	$P_D$	1.2	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55 ~ +150	°C

### Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4		-1.0	V
Drain-source on-resistance <sup>1)</sup>	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -3.5A$			64	mΩ
		$V_{GS} = -2.5V, I_D = -3.0A$			80	
		$V_{GS} = -1.8V, I_D = -2.5A$			110	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		550		pF
Output Capacitance	$C_{oss}$			89		
Reverse Transfer Capacitance	$C_{rss}$			65		
Total Gate Charge	$Q_g$	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -3.5A$		4.3		nC
Gate-Source Charge	$Q_{gs}$			0.8		
Gate-Drain Charge	$Q_{gd}$			1.1		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10V, V_{GS} = -4.5V, I_D = -1A, R_{GEN} = 2.5\Omega$		12		nS
Turn-on rise time	$t_r$			54		
Turn-off delay time	$t_{d(off)}$			15		
Turn-off fall time	$t_f$			9		
<b>Source-Drain Diode characteristics</b>						
Diode Forward Current <sup>1)</sup>	$I_S$				-4.0	A
Diode Forward voltage	$V_{DS}$	$V_{GS} = 0V, I_S = -4.0A$			-1.2	V

Notes:

- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

## Typical Characteristics

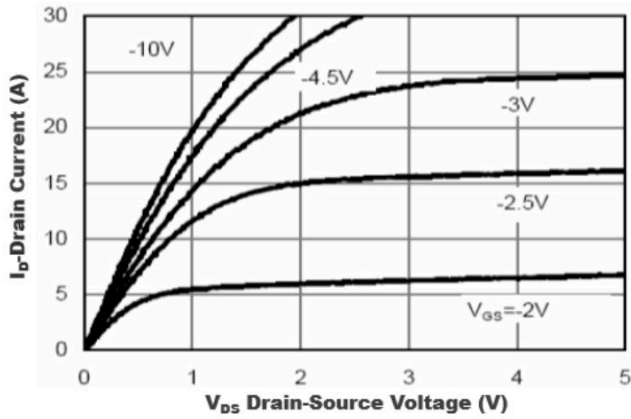


Figure1. Output Characteristics

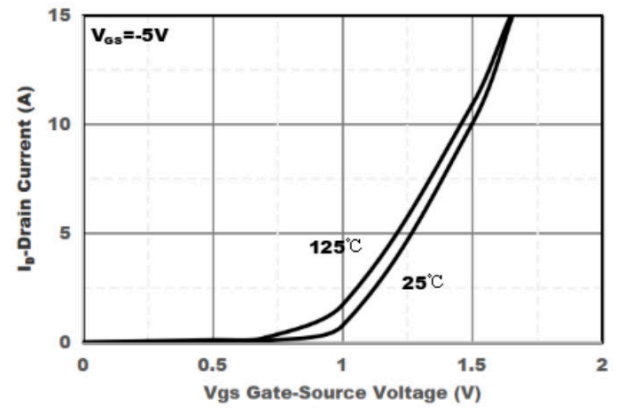


Figure2. Transfer Characteristics

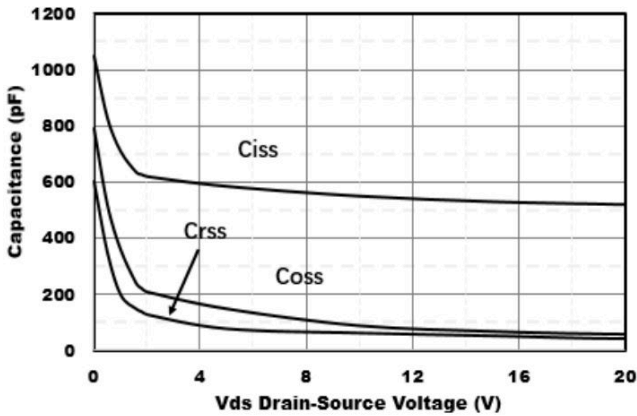


Figure3. Capacitance Characteristics

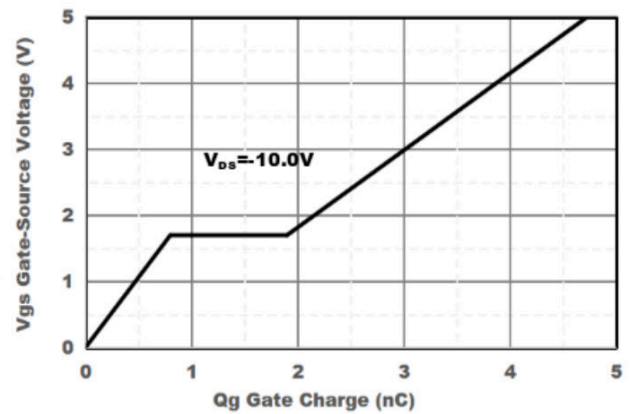


Figure4. Gate Charge

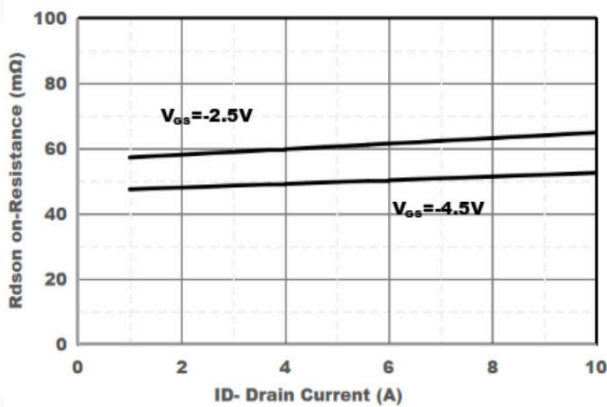


Figure5. Drain-Source on Resistance

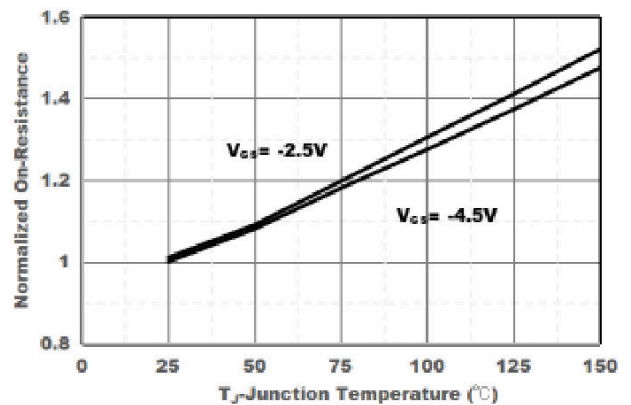
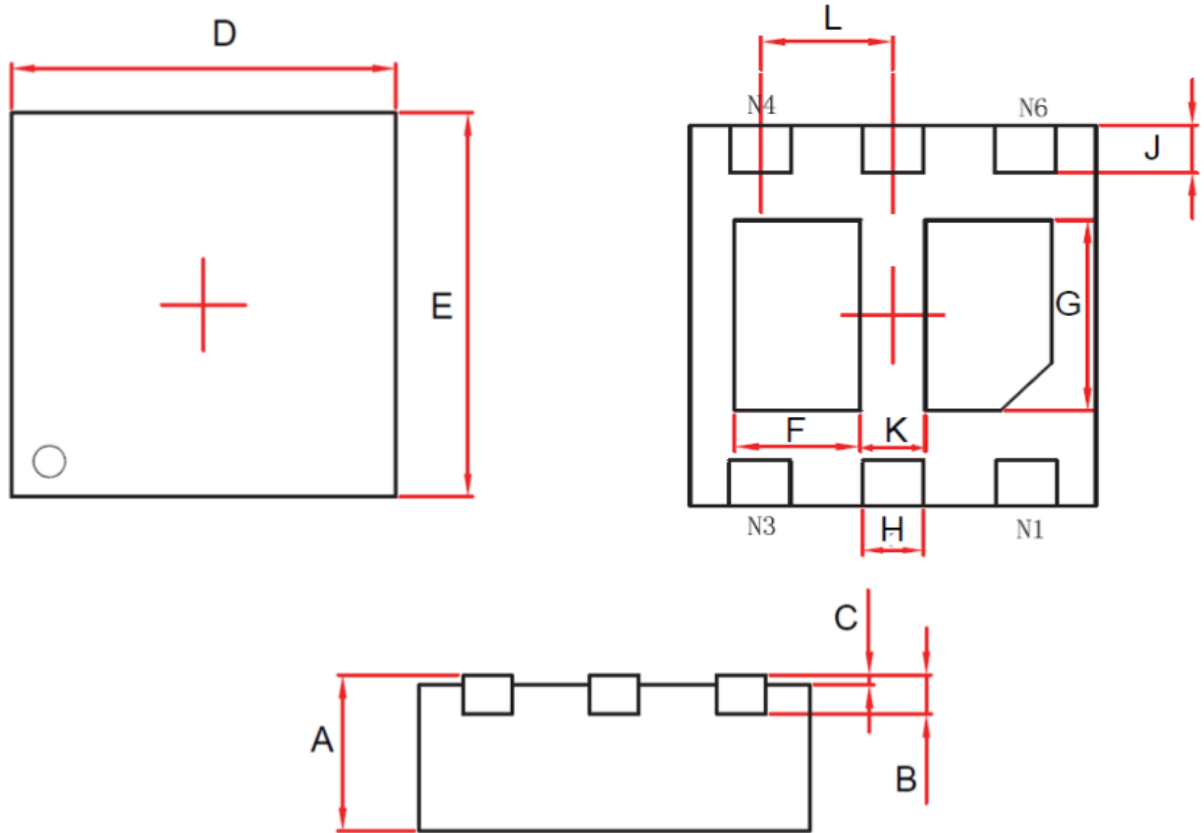


Figure6. Drain-Source on Resistance

### DFN2\*2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.750	0.850	0.030	0.034
B	0.200 REF.		0.008 REF.	
C	0.000	0.050	0.000	0.002
D	1.950	2.050	0.077	0.081
E	1.950	2.050	0.077	0.081
F	0.440	0.690	0.017	0.027
G	0.840	1.090	0.033	0.043
H	0.250	0.350	0.010	0.014
J	0.175	0.375	0.007	0.015
K	0.250	0.350	0.010	0.014
L	0.650 TYP.		0.026 TYP.	